

Supporting Information for

**Highly efficient flexible quantum-dot light emitting diodes
with an ITO/Ag/ITO cathode**

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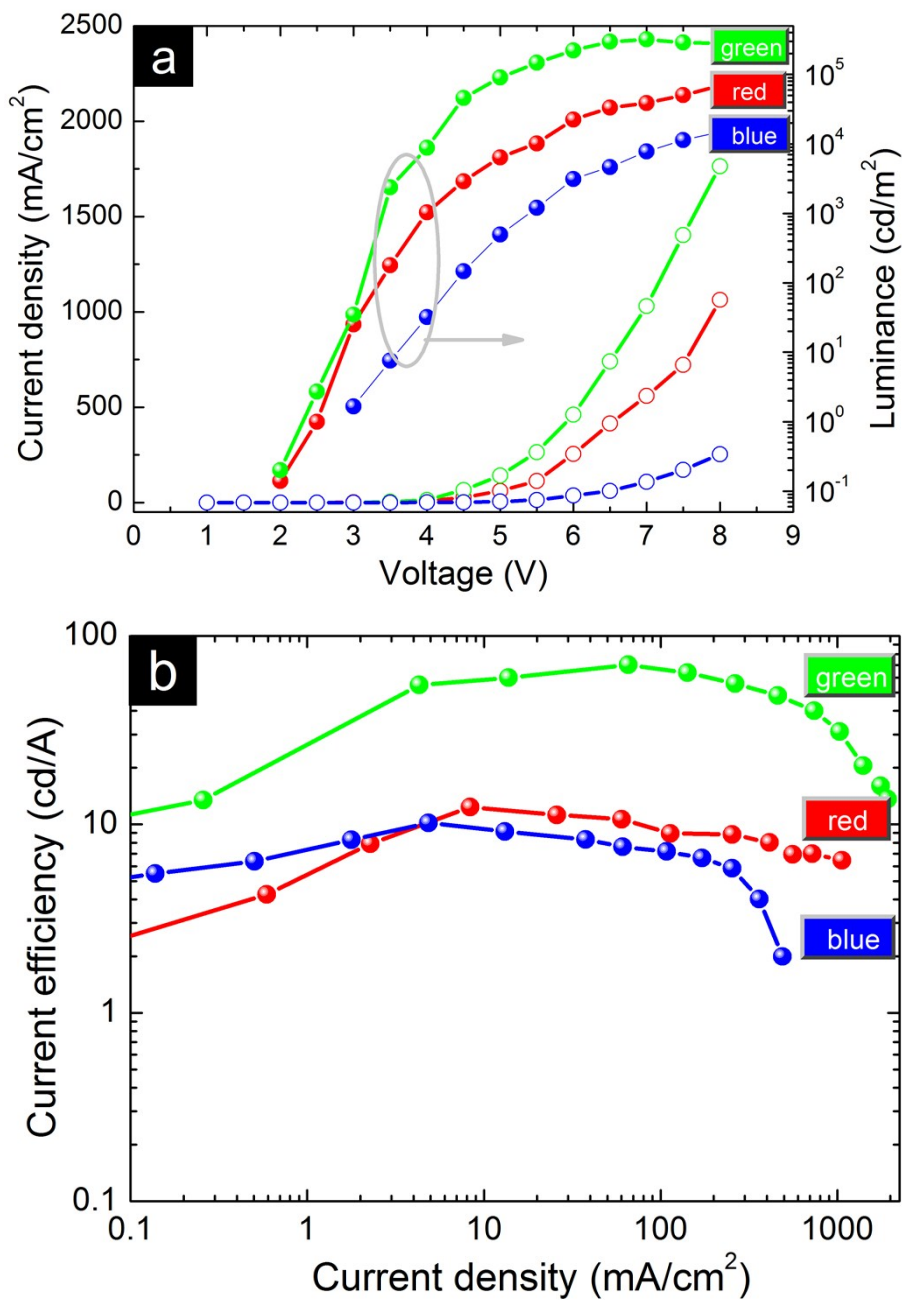


Figure S1. (a) Current density-voltage-luminance and (b) current density-efficiency properties for RGB QLEDs with glass/ITO as the cathodes

Figure S1 shows the optical-electrical characteristics of the glass/ITO based QLEDs. We can see that the maximum current efficiencies of 12.3, 65.5, and 10.2 cd/A are obtained for RGB QLEDs, respectively, with the peak luminance of 68580, 319768, and 14820 cd/m^2 for corresponding devices. It is worth to noting that the performances of glass/ITO based devices are all lower than that of flexible device

with PET/IAI cathodes. The turn-on voltages (the turn-on voltage is defined as the voltage under which the device luminance is 1 cd/m²) are approximate 2.2, 2.4 and 2.9 V for RGB QLEDs, respectively, which are similar to that of PET/IAI based devices due to the good electron injection and transport capability of ZnO layer.